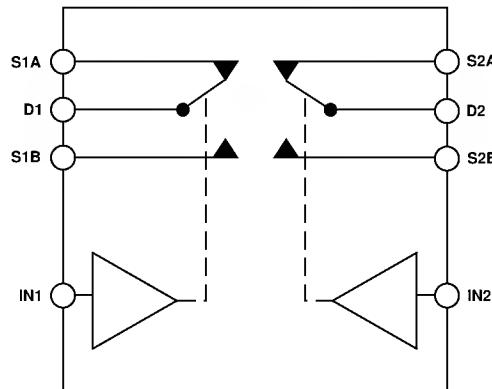


**FEATURES**

**44 V Supply Maximum Ratings**  
 **$V_{SS}$  to  $V_{DD}$  Analog Signal Range**  
**Low On Resistance (12  $\Omega$  typ)**  
**Low  $\Delta R_{ON}$  (3  $\Omega$  max)**  
**Low  $R_{ON}$  Match (2.5  $\Omega$  max)**  
**Low Power Dissipation**  
**Fast Switching Times**  
 $t_{ON} < 175$  ns  
 $t_{OFF} < 145$  ns  
**Low Leakage Currents (5 nA max)**  
**Low Charge Injection (10 pC max)**  
**Break-Before-Make Switching Action**

**APPLICATIONS**

**Audio and Video Switching**  
**Battery Powered Systems**  
**Test Equipment**  
**Communications Systems**

**FUNCTIONAL BLOCK DIAGRAM**

**GENERAL DESCRIPTION**

The ADG436 is a monolithic CMOS device comprising two independently selectable SPDT switches. It is designed on an LC<sup>2</sup>MOS process which provides low power dissipation yet gives high switching speed and low on resistance.

The on resistance profile is very flat over the full analog input range ensuring good linearity and low distortion when switching audio signals. High switching speed also makes the part suitable for video signal switching. CMOS construction ensures ultralow power dissipation making the part ideally suited for portable and battery powered instruments.

Each switch conducts equally well in both directions when ON and has an input signal range which extends to the power supplies. In the OFF condition, signal levels up to the supplies are blocked. All switches exhibit break-before-make switching action for use in multiplexer applications. Inherent in the design is low charge injection for minimum transients when switching the digital inputs.

**PRODUCT HIGHLIGHTS**

1. Extended Signal Range  
The ADG436 is fabricated on an enhanced LC<sup>2</sup>MOS process, giving an increased signal range which extends to the supply rails.
2. Low Power Dissipation
3. Low  $R_{ON}$
4. Single Supply Operation  
For applications where the analog signal is unipolar, the ADG436 can be operated from a single rail power supply.

**REV. 0**

Information furnished by Analog Devices is believed to be accurate and reliable. However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices.

© Analog Devices, Inc., 1996

One Technology Way, P.O. Box 9106, Norwood, MA 02062-9106, U.S.A.  
 Tel: 617/329-4700 Fax: 617/326-8703

# ADG436- SPECIFICATIONS<sup>1</sup>

Dual Supply ( $V_{DD} = +15$  V,  $V_{SS} = -15$  V, GND = 0 V, unless otherwise noted)

Parameter	+25°C	-40°C to +85°C	Units	Test Conditions/Comments
ANALOG SWITCH				
Analog Signal Range				
$R_{ON}$	12	$V_{SS}$ to $V_{DD}$	V	$V_D = \pm 10$ V, $I_S = -1$ mA
$\Delta R_{ON}$	1	25	$\Omega$ typ	$V_D = -5$ V, 5 V, $I_S = -10$ mA
$R_{ON}$ Match	1	3	$\Omega$ max	$V_D = \pm 10$ V, $I_S = -10$ mA
		2.5	$\Omega$ typ	
			$\Omega$ max	
LEAKAGE CURRENTS				
Source OFF Leakage $I_S$ (OFF)	$\pm 0.005$		nA typ	$V_{DD} = +16.5$ V, $V_{SS} = -16.5$ V
	$\pm 0.25$		nA max	$V_D = \pm 15.5$ V, $V_S = \pm 15.5$ V
Channel ON Leakage $I_D$ , $I_S$ (ON)	$\pm 0.05$	$\pm 5$	nA typ	Test Circuit 2
	$\pm 0.4$	$\pm 5$	nA max	$V_S = V_D = \pm 15.5$ V
				Test Circuit 3
DIGITAL INPUTS				
Input High Voltage, $V_{INH}$		2.4	V min	
Input Low Voltage, $V_{INL}$		0.8	V max	
Input Current				
$I_{INL}$ or $I_{INH}$		$\pm 0.005$	$\mu A$ typ	
		$\pm 0.5$	$\mu A$ max	$V_{IN} = 0$ V or $V_{DD}$
DYNAMIC CHARACTERISTICS <sup>2</sup>				
$t_{ON}$	70	125	ns typ	$R_L = 300 \Omega$ , $C_L = 35$ pF;
			ns max	$V_S = \pm 10$ V; Test Circuit 4
$t_{OFF}$	60	120	ns typ	$R_L = 300 \Omega$ , $C_L = 35$ pF;
			ns max	$V_S = \pm 10$ V; Test Circuit 4
Break-Before-Make Delay, $t_{OPEN}$	10		ns min	$R_L = 300 \Omega$ , $C_L = 35$ pF;
				$V_S = +5$ V; Test Circuit 5
Charge Injection	10		pC typ	$V_D = 0$ V, $R_D = 0 \Omega$ , $C_L = 10$ nF;
				Test Circuit 6;
OFF Isolation	72		dB typ	$R_L = 75 \Omega$ , $C_L = 5$ pF, $f = 1$ MHz;
				$V_S = 2.3$ V rms, Test Circuit 7
Channel-to-Channel Crosstalk	90		dB typ	$R_L = 75 \Omega$ , $C_L = 5$ pF, $f = 1$ MHz;
				$V_S = 2.3$ V rms, Test Circuit 8
$C_S$ (OFF)	10		pF typ	
$C_D$ , $C_S$ (ON)	30		pF typ	
POWER REQUIREMENTS				
$I_{DD}$	0.05	0.35	mA typ	Digital Inputs = 0 V or 5 V
			mA max	
$I_{SS}$	0.01	5	$\mu A$ typ	
	1	$\pm 3/\pm 20$	$\mu A$ max	
$V_{DD}/V_{SS}$			V min/V max	$ V_{DD}  =  V_{SS} $

## NOTES

<sup>1</sup>Temperature Range is as follows: B Version, -40°C to +85°C.

<sup>2</sup>Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

**Single Supply** ( $V_{DD} = +12$  V,  $V_{SS} = 0$  V,  $GND = 0$  V, unless otherwise noted)

Parameter	+25°C	-40°C to +85°C	Units	Test Conditions/Comments
ANALOG SWITCH				
Analog Signal Range				
$R_{ON}$	20	0 to $V_{DD}$ 40 2.5	V $\Omega$ typ $\Omega$ max $\Omega$ max	$V_D = +1$ V, +10 V, $I_S = -1$ mA
$R_{ON}$ Match				
LEAKAGE CURRENTS				
Source OFF Leakage $I_S$ (OFF)	$\pm 0.005$ $\pm 0.25$	$\pm 5$	nA typ nA max	$V_{DD} = +13.2$ V $V_D = 12.2$ V/1 V, $V_S = 1$ V/12.2 V Test Circuit 2
Channel ON Leakage $I_D$ , $I_S$ (ON)	$\pm 0.05$ $\pm 4$	$\pm 5$	nA typ nA max	$V_S = V_D = 12.2$ V/1 V Test Circuit 3
DIGITAL INPUTS				
Input High Voltage, $V_{INH}$		2.4	V min	
Input Low Voltage, $V_{INL}$		0.8	V max	
Input Current				
$I_{INL}$ or $I_{INH}$		$\pm 0.005$ $\pm 0.5$	$\mu$ A typ $\mu$ A max	$V_{IN} = 0$ V or $V_{DD}$
DYNAMIC CHARACTERISTICS <sup>2</sup>				
$t_{ON}$	100	200	ns typ ns max	$R_L = 300 \Omega$ , $C_L = 35$ pF; $V_S = +8$ V; Test Circuit 4
$t_{OFF}$	90	180	ns typ ns max	$R_L = 300 \Omega$ , $C_L = 35$ pF; $V_S = +8$ V; Test Circuit 4
Break-Before-Make Delay, $t_{OPEN}$	10		ns typ	$R_L = 300 \Omega$ , $C_L = 35$ pF; $V_S = +5$ V; Test Circuit 5
Charge Injection	10		pC typ	$V_D = 6$ V, $R_D = 0$ $\Omega$ , $C_L = 10$ nF; Test Circuit 6
OFF Isolation	72		dB typ	$R_L = 75 \Omega$ , $C_L = 5$ pF, $f = 1$ MHz; $V_S = 1.15$ V rms; Test Circuit 7
Channel-to-Channel Crosstalk	90		dB typ	$R_L = 75 \Omega$ , $C_L = 5$ pF, $f = 1$ MHz; $V_S = 1.15$ V rms, Test Circuit 8
$C_S$ (OFF)	10		pF typ	
$C_D$ , $C_S$ (ON)	30		pF typ	
POWER REQUIREMENTS				
$I_{DD}$	0.05	0.35 +3/+30	mA typ mA max	$V_{DD} = +13.5$ V
$V_{DD}$			V min/V max	Digital Inputs = 0 V or 5 V

## NOTES

<sup>1</sup>Temperature range is as follows: B Version, -40°C to +85°C.<sup>2</sup>Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

# ADG436

## ABSOLUTE MAXIMUM RATINGS<sup>1</sup>

(T<sub>A</sub> = +25°C unless otherwise noted)

V <sub>DD</sub> to V <sub>SS</sub> .....	+44 V
V <sub>DD</sub> to GND .....	-0.3 V to +30 V
V <sub>SS</sub> to GND .....	+0.3 V to -30 V
Analog, Digital Inputs <sup>2</sup> .....	V <sub>SS</sub> - 2 V to V <sub>DD</sub> + 2 V or 20 mA, whichever occurs first
Continuous Current, S or D .....	20 mA
Peak Current, S or D .....	40 mA (Pulsed at 1 ms, 10% Duty Cycle max)
Operating Temperature Range	
Industrial (B Version) .....	-40°C to +85°C
Storage Temperature Range .....	-65°C to +125°C
Junction Temperature .....	+150°C
Plastic DIP Package	
θ <sub>JA</sub> , Thermal Impedance .....	117°C/W
Lead Temperature, Soldering (10 sec) .....	+260°C

## SOIC Package

θ <sub>JA</sub> , Thermal Impedance .....	77°C/W
Lead Temperature, Soldering	
Vapor Phase (60 sec) .....	+215°C
Infrared (15 sec) .....	+220°C

## NOTES

<sup>1</sup>Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.

<sup>2</sup>Overvoltages at IN, S or D will be clamped by internal diodes. Current should be limited to the maximum ratings given.

## CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the ADG436 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



ADG436 Truth Table

Logic	Switch A	Switch B
0	OFF	ON
1	ON	OFF

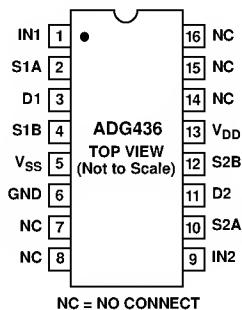
ORDERING GUIDE

Model	Temperature Range	Package Option*
ADG436BN	-40°C to +85°C	N-16
ADG436BR	-40°C to +85°C	R-16A

\*N = Plastic DIP, R-16A = 0.15" Small Outline IC (SOIC).

## TERMINOLOGY

$V_{DD}$	Most positive power supply potential.	$t_{ON}$	Delay between applying the digital control input and the output switching on.
$V_{SS}$	Most negative power supply potential in dual supplies. In single supply applications, it may be connected to ground.	$t_{OFF}$	Delay between applying the digital control input and the output switching off.
GND	Ground (0 V) reference.	$t_{OPEN}$	Break-before-make delay when switches are configured as a multiplexer.
S	Source terminal. May be an input or output.	$V_{INL}$	Maximum input voltage for logic "0."
D	Drain terminal. May be an input or output.	$V_{INH}$	Minimum input voltage for logic "1."
IN	Logic control input.	$I_{INL} (I_{INH})$	Input current of the digital input.
$R_{ON}$	Ohmic resistance between D and S.	Crosstalk	A measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance.
$\Delta R_{ON}$	$R_{ON}$ variation due to a change in the analog input voltage with a constant load current.	Off	A measure of unwanted signal coupling through an "OFF" switch.
$R_{ON}$ Match	Difference between the $R_{ON}$ of any two channels.	Charge Injection	A measure of the glitch impulse transferred from the digital input to the analog output during switching.
$I_S$ (OFF)	Source leakage current with the switch "OFF."	$I_{DD}$	Positive supply current.
$I_D$ (OFF)	Drain leakage current with the switch "OFF."	$I_{SS}$	Negative supply current.
$I_D, I_S$ (ON)	Channel leakage current with the switch "ON."		
$V_D$ ( $V_S$ )	Analog voltage on terminals D, S.		
$C_S$ (OFF)	"OFF" switch source capacitance.		
$C_D$ (OFF)	"OFF" switch drain capacitance.		
$C_D, C_S$ (ON)	"ON" switch capacitance.		

PIN CONFIGURATION  
(DIP/SOIC)

# ADG436- Typical Performance Graphs

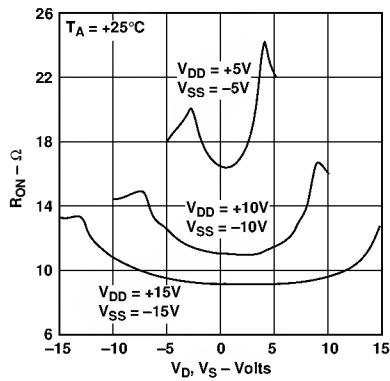


Figure 1.  $R_{ON}$  as a Function of  $V_D$  ( $V_S$ ): Dual Supply

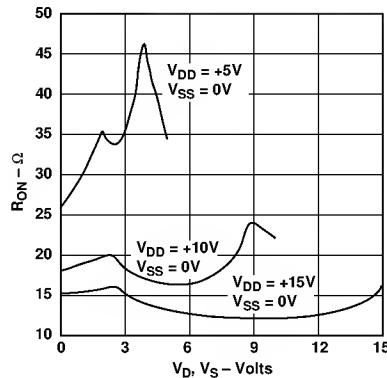


Figure 2.  $R_{ON}$  as a Function of  $V_D$  ( $V_S$ ): Single Power Supply

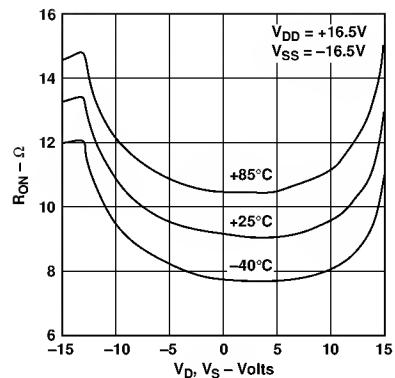


Figure 3.  $R_{ON}$  as a Function of  $V_D$  ( $V_S$ ) for Different Temperatures: Dual Supply

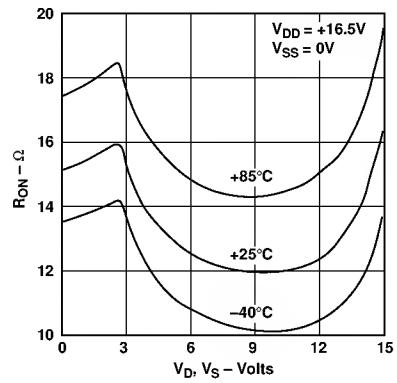


Figure 4.  $R_{ON}$  as a Function of  $V_D$  ( $V_S$ ) for Different Temperatures: Single Supply

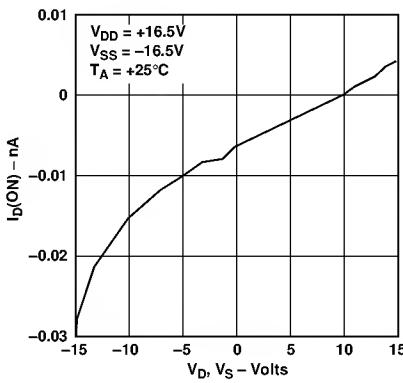


Figure 5.  $I_D$  (ON) Leakage Current as a Function of  $V_D$  ( $V_S$ ): Dual Supply

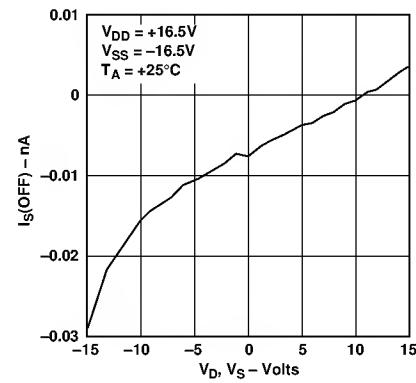


Figure 6.  $I_S$  (OFF) Leakage Current as a Function of  $V_D$  ( $V_S$ ): Dual Supply

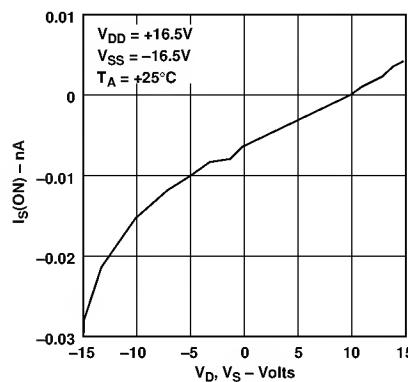


Figure 7.  $I_S$  (ON) Leakage Current as a Function of  $V_D$  ( $V_S$ ): Dual Supply

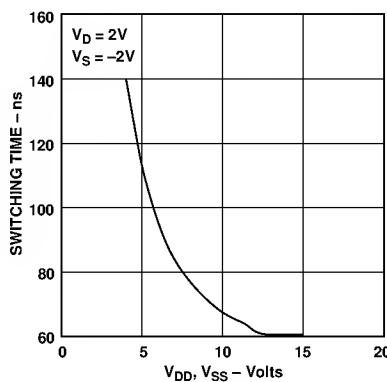


Figure 8. Switching Time as a Function of  $V_D$  ( $V_S$ ): Dual Supply

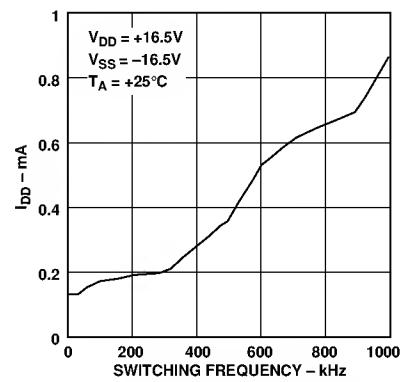
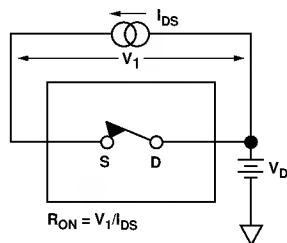
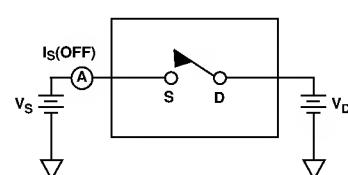


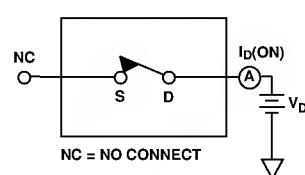
Figure 9.  $I_{DD}$  as a Function of Switching Frequency: Dual Supply



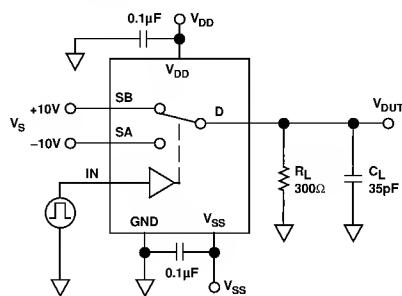
*Test Circuit 1. On Resistance*



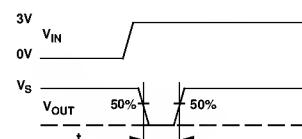
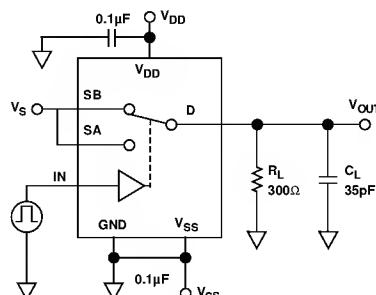
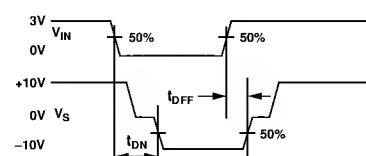
*Test Circuit 2. Off Leakage*



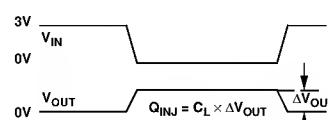
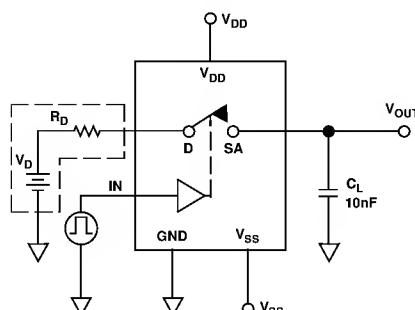
*Test Circuit 3. On Leakage*



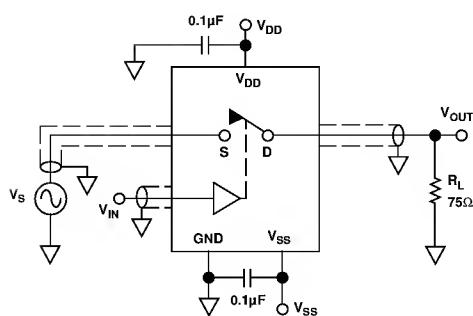
*Test Circuit 4. Switching Times*



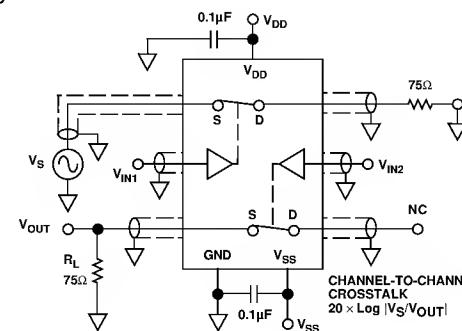
*Test Circuit 5. Break-Before-Make Delay,  $t_{OPEN}$*



*Test Circuit 6. Charge Injection*



*Test Circuit 7. Off Isolation*



*Test Circuit 8. Channel-to-Channel Crosstalk*

# ADG436

## APPLICATIONS INFORMATION

### ADG436 Supply Voltages

The ADG436 can operate off a dual or single supply.  $V_{SS}$  should be connected to GND when operating with a single supply. When using a dual supply, the ADG436 can also operate with unbalanced supplies, for example  $V_{DD} = 20$  V and  $V_{SS} = -5$  V. The only restrictions are that  $V_{DD}$  to GND must not exceed 30 V,  $V_{SS}$  to GND must not drop below -30 V and  $V_{DD}$  to  $V_{SS}$  must not exceed +44 V. It is important to remember that the ADG436 supply voltage directly affects the input signal range, the switch ON resistance and the switching times of the part. The effects of the power supplies on these characteristics can be clearly seen from the characteristic curves in this data sheet.

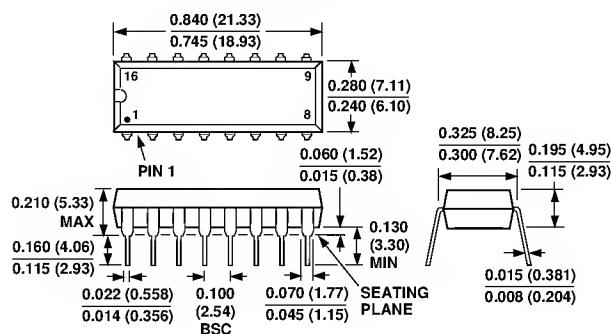
### Power-Supply Sequencing

When using CMOS devices, care must be taken to ensure correct power-supply sequencing. Incorrect power-supply sequencing can result in the device being subjected to stresses beyond those maximum ratings listed in the data sheet. Always sequence  $V_{DD}$  on first followed by  $V_{SS}$  and the logic signals. An external signal can then be safely presented to the source or drain of the switch.

## MECHANICAL INFORMATION

Dimensions are shown in inches and (mm).

### 16-Pin Plastic DIP (N-16)



### 16-Pin Narrow Body SOIC (R-16A)

